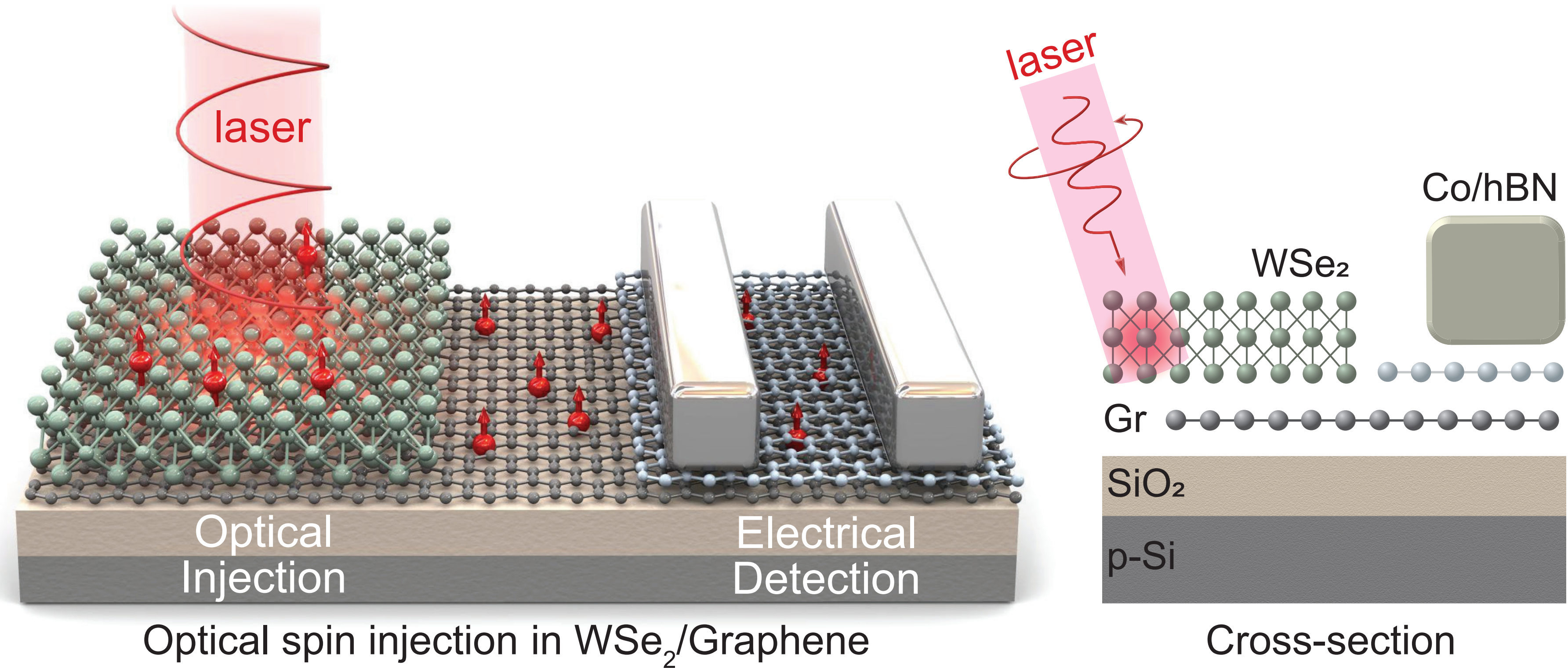


1. Introduction

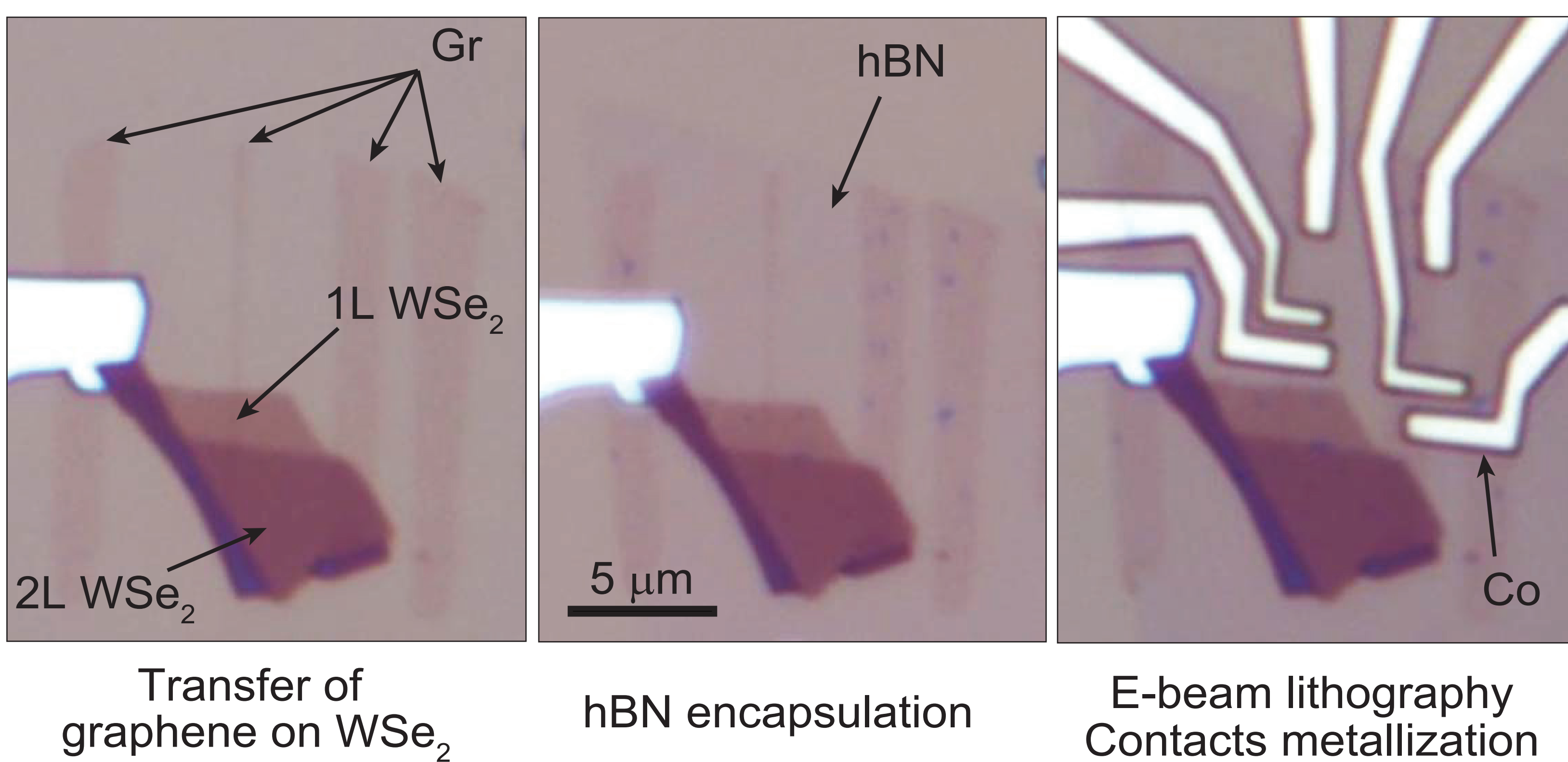
We demonstrate here possibility of nondestructive direct optical spin injection into graphene through a 2D semiconducting monolayer crystal, by following scheme:

- Circularly polarized light selectively addresses carrier valley degree of freedom in the monolayer WSe₂ crystal;
- Spin-valley locking in the crystal with broken inversion symmetry leads to non-equilibrium spin concentration;
- Carriers tunnel into the superjacent graphene layer and diffuse over a 3.5 μm distance;
- Spin transport is detected electrically using Co/hBN contacts in a nonlocal geometry.

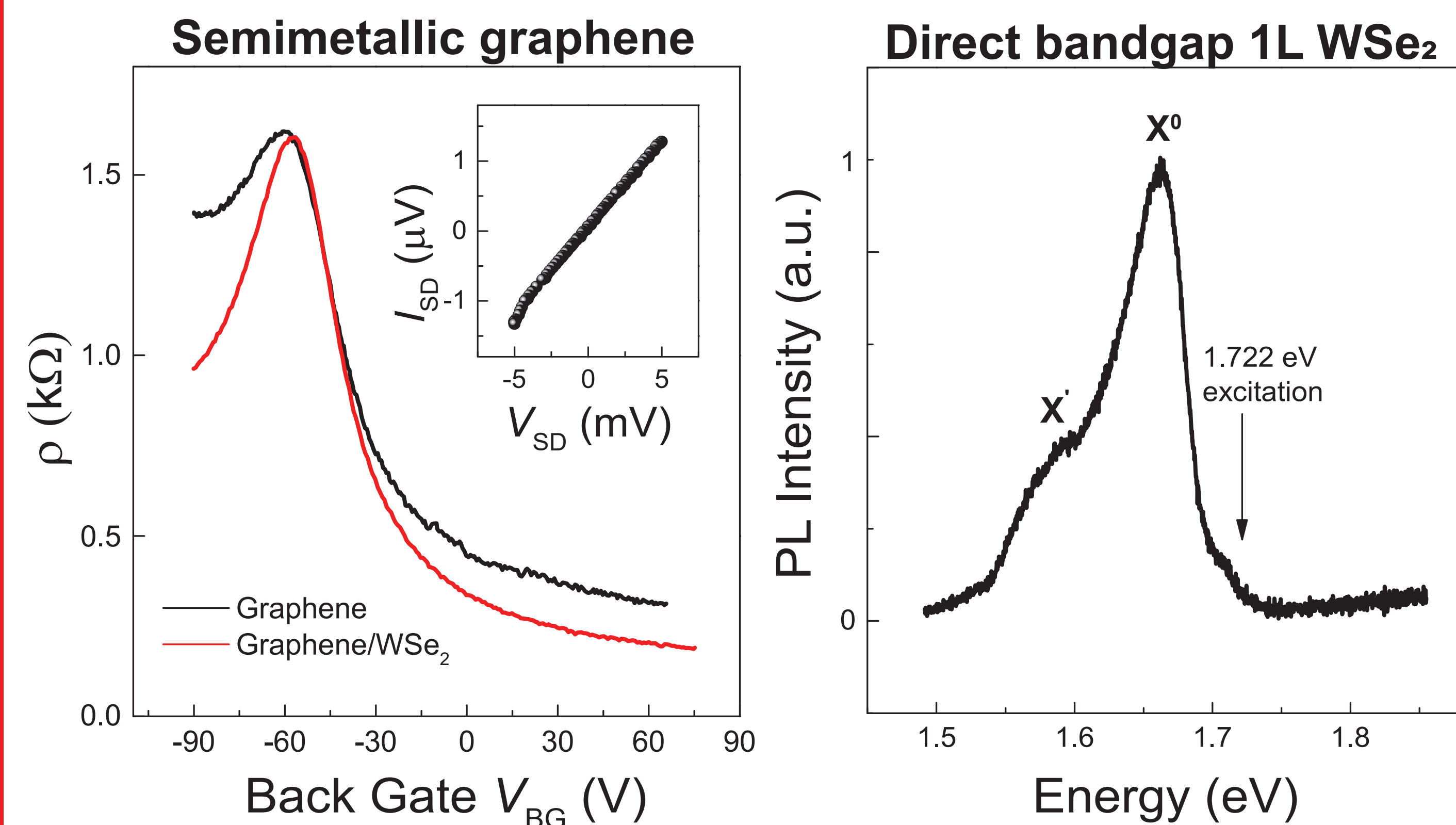
2. Device structure



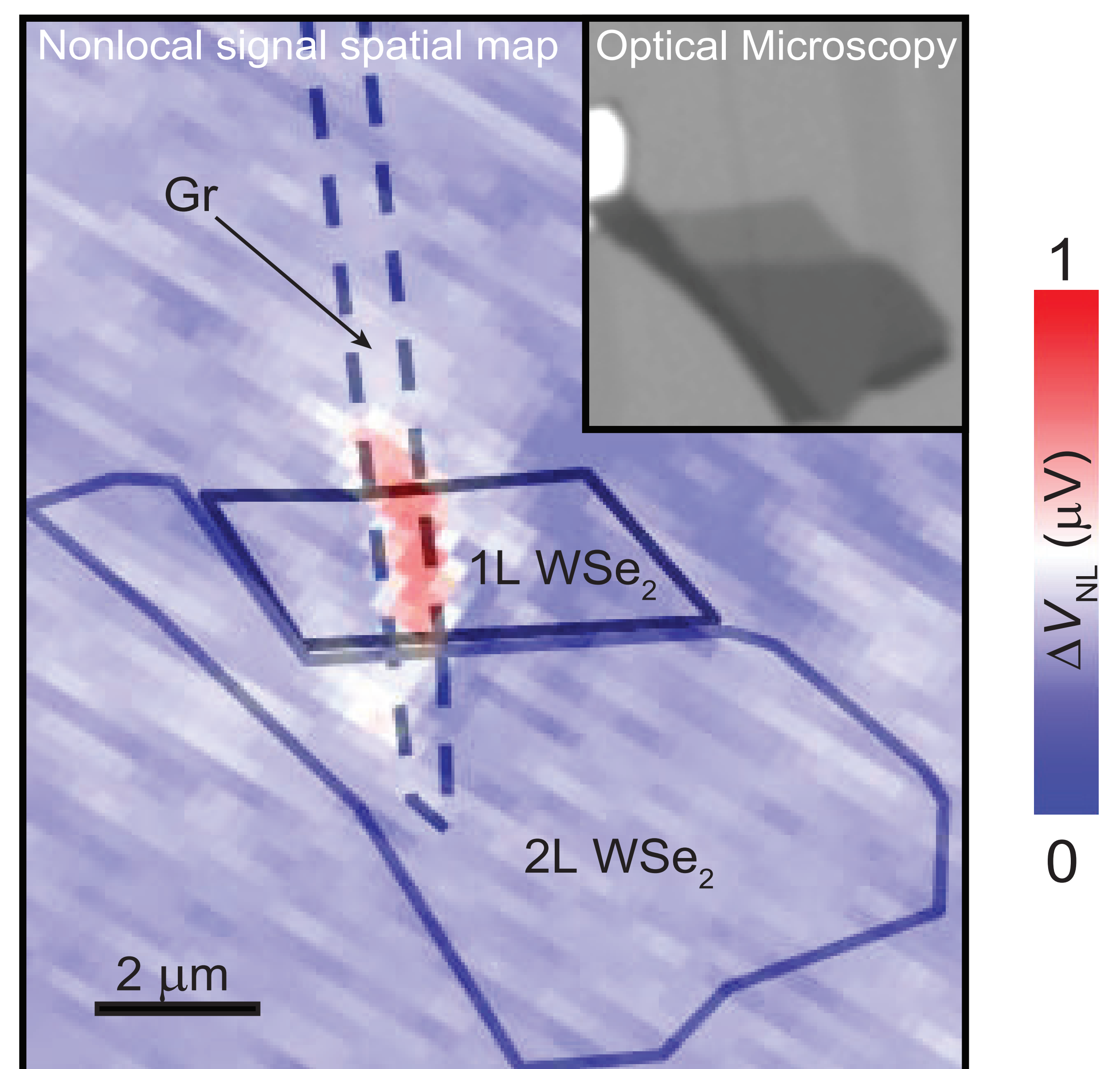
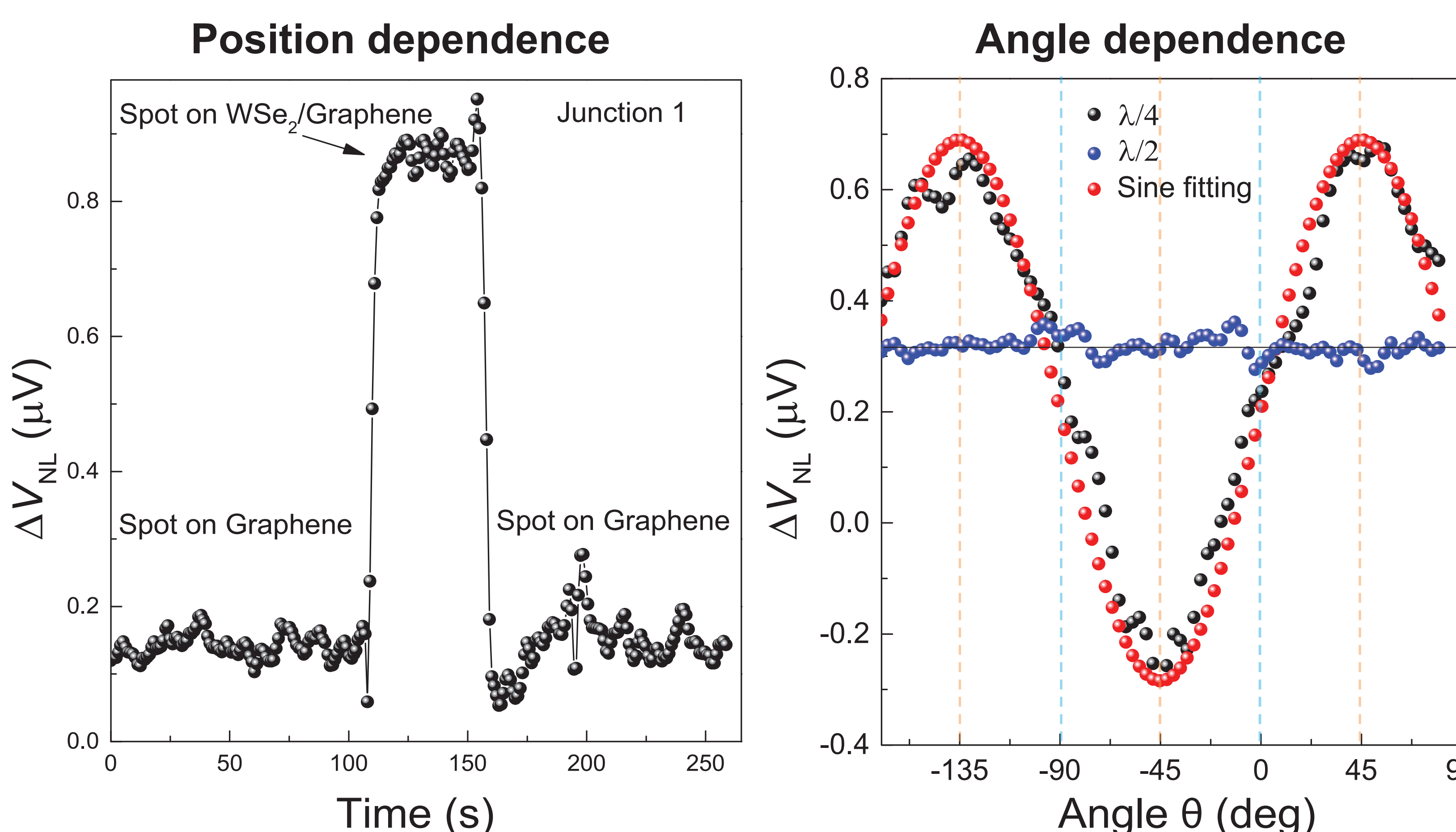
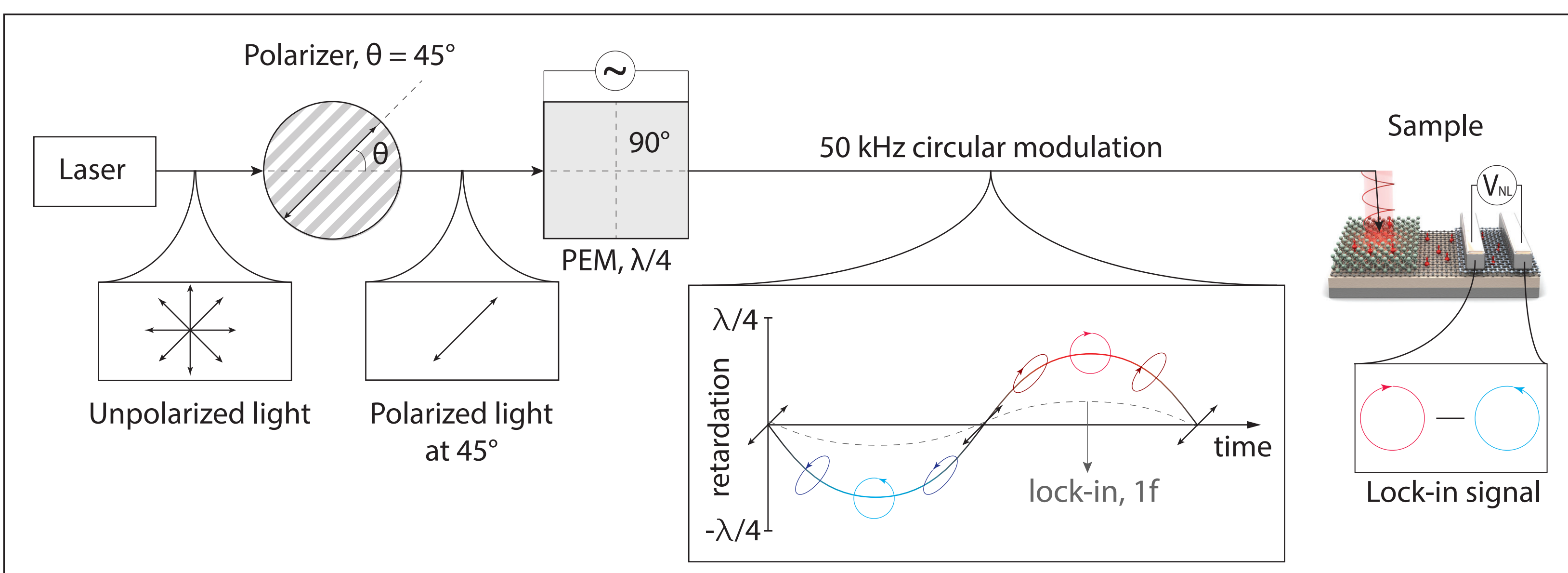
3. Device microfabrication



4. Material characterisation



5. Optospintronic measurements



Circularly modulated light focused on the WSe₂ results in nonlocal spin signal detected by lock-in amplifier. We obtain following results:

- Well pronounced nonlocal signal from the heterostructure region
- Neither bilayer WSe₂ nor graphene alone shows spin signal
- Linear power dependency up to 8 mW incident laser intensity
- Absence of the signal in the case of linearly polarized light

6. Conclusion

- Demonstration of the first optical spin injection in graphene by exploiting spin-valley selective absorption of monolayer WSe₂.
- Angle dependence measurements together with the absence of non-local signal at the bilayer WSe₂/graphene interface proves spin-coupled, valley-selective origin of the observed signal.

Reference

Ahmet Avsar, Dmitrii Unuchek, et al. Optospintronics in Graphene via Proximity Coupling. ACS Nano 11, 11678–11686 (2017). DOI: 10.1021/acsnano.7b06800

Acknowledgement

